

L-93DP3C

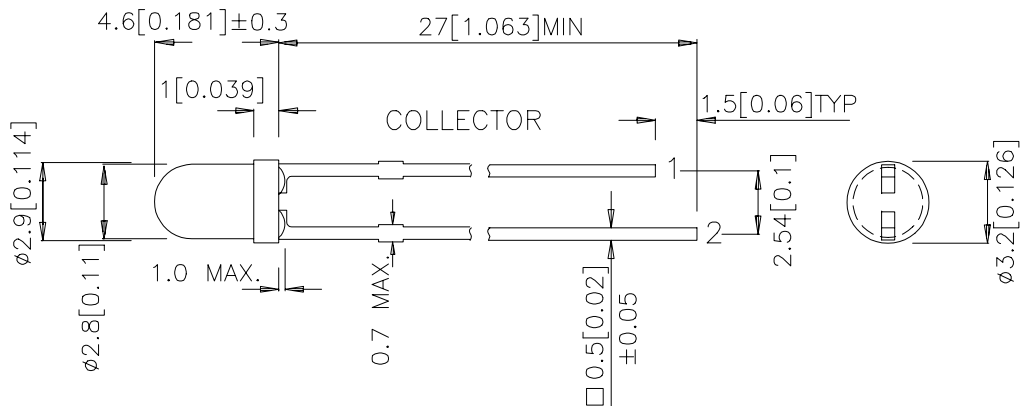
Features

- MECHANICALLY AND SPECTRALLY MATCHED TO THE INFRARED EMITTING LED LAMP.
- WATER CLEAR LENS.

Description

P3 Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Electrical \ Radiant Characteristics at $T_A=25^{\circ}\text{C}$

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{BRCEO}	Collector-to-Emitter Breakdown Voltage	30	-	-	V	$I_C=100\mu\text{A}$, $E_e=0\text{mW}/\text{cm}^2$
V_{BRECO}	Emitter-to-Collector Breakdown Voltage	5	-	-	V	$I_E=100\mu\text{A}$, $E_e=0\text{mW}/\text{cm}^2$
$V_{CE(SAT)}$	Collector-to-Emitter Saturation Voltage	-	-	0.8	V	$I_C=2\text{mA}$, $E_e=20\text{mW}/\text{cm}^2$
I_{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE}=10\text{V}$, $E_e=0\text{mW}/\text{cm}^2$
T_R	Rise Time (10% to 90%)	-	3	-	us	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$, $R_L=1000\Omega$
T_F	Fall Time (90% to 10%)	-	3	-	us	
C_{CB}	Collector-base Capacitance	-	6.4		pF	$F=1\text{MHZ}$ $V_{CB}=3\text{V}$
λ_{SMAX}	Wavelength of the max sensitivity	-	940		nm	
$I_{(ON)}$	On State Collector Current	0.2	0.6	-	mA	$V_{CE}=5\text{V}$, $E_e=1\text{mW}/\text{cm}^2$, $\lambda=940\text{nm}$

Absolute Maximum Ratings at $T_A=25^{\circ}\text{C}$

Parameter	Maximum Rating
Power dissipation	100mW
Operating Temperature Range	-40°C To +85°C
Storage Temperature Range	-40°C To +85°C
Lead Solder Temperature [1]	260°C For 5 Seconds

Note:

1. 2mm below package base.